

TRANSISTOR (PNP)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

$$P_{CM}: 1.25W (T_{amb}=25^{\circ}C)$$

Collector current

$$I_{CM}: -3A$$

Collector-base voltage

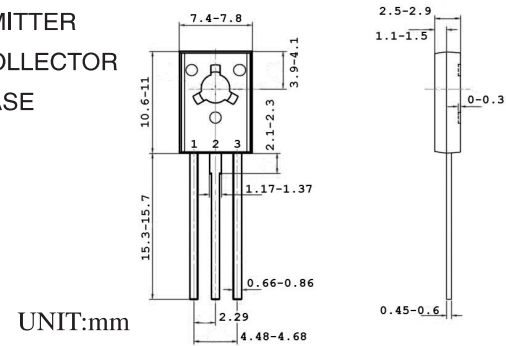
$$V_{(BR)CBO}: -40V$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}C \text{ to } +150^{\circ}C$$

TO-126

1. EMITTER
2. COLLECTOR
3. BASE


MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100 \mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100 \mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$		-1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-30V, I_B=0$		-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$		-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-1A$	60	400	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-100mA$	32		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-2A, I_B=-0.2A$		-0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-2A, I_B=-0.2A$		-2	V
Transition frequency	f_r	$V_{CE}=-5V, I_C=-0.1A$ $f=10MHz$	50		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400